

FIG. 1

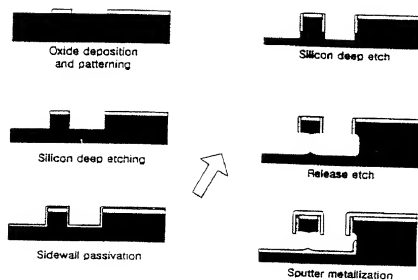


FIG. 2

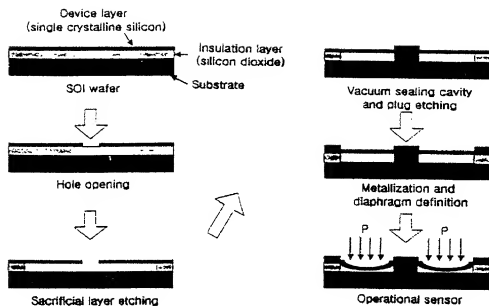




FIG. 4

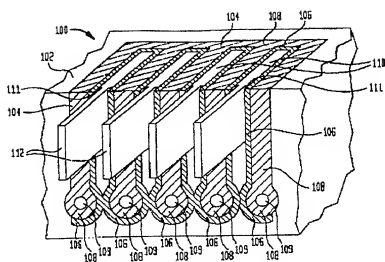


FIG. 5



First etch mask deposition and patterning



Deep silicon etching to form trenches



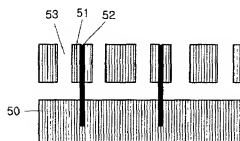
Trench filling by oxidation



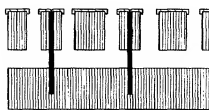
Top oxide removal



Second etch mask deposition and patterning



Structure fabrication



Metallization

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FIG. 6

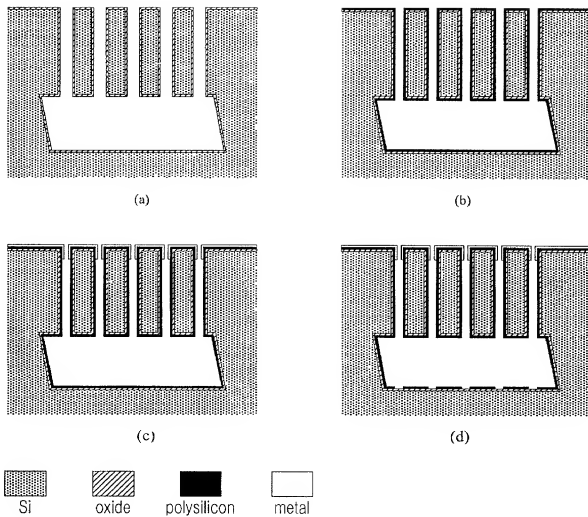
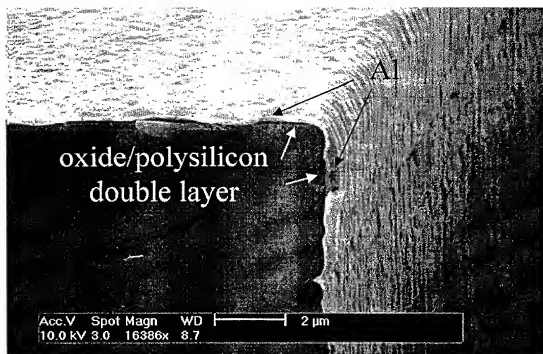
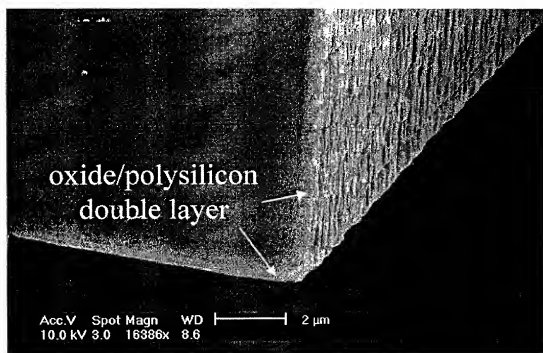


FIG. 7



(a)



(b)

FIG. 8

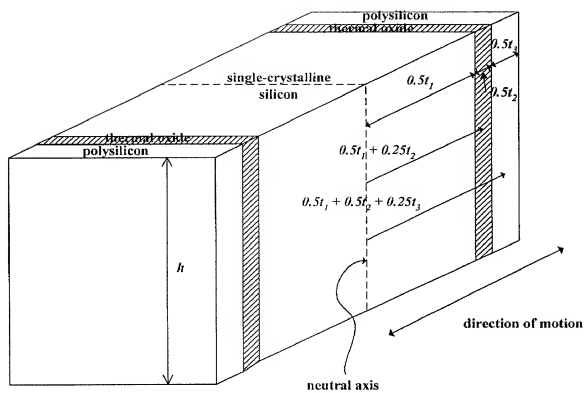




FIG. 9

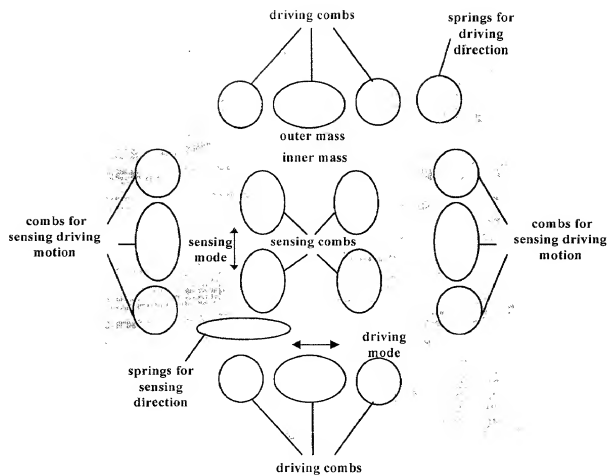


FIG. 10

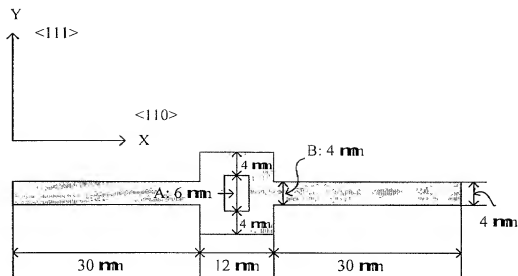


FIG. 11

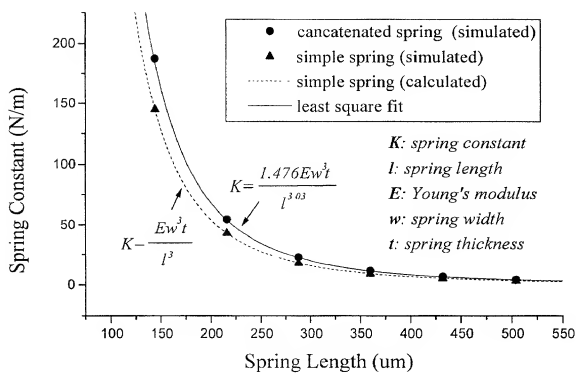
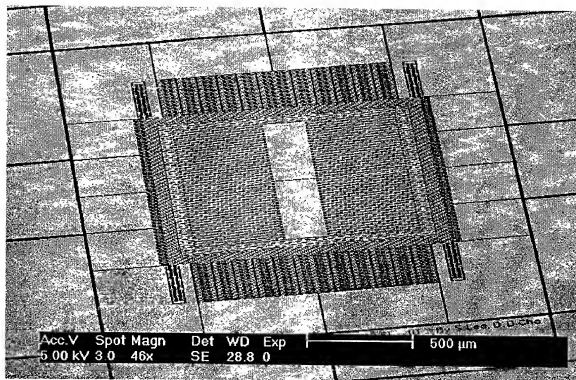
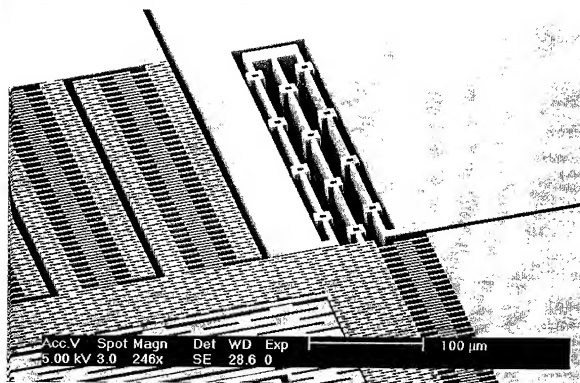


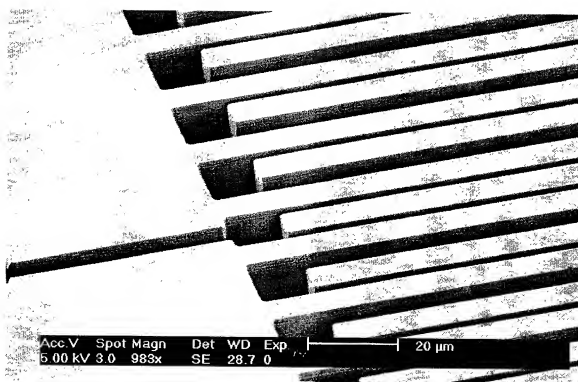
FIG. 12



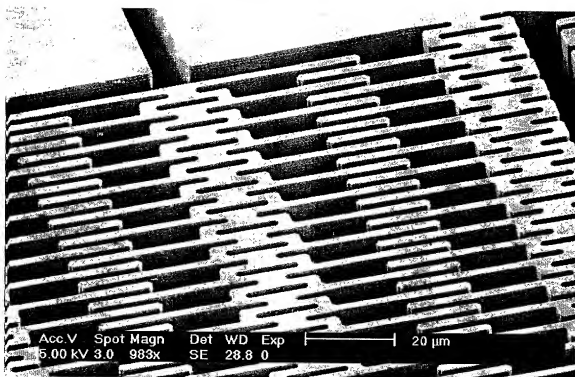
(a)



(b)

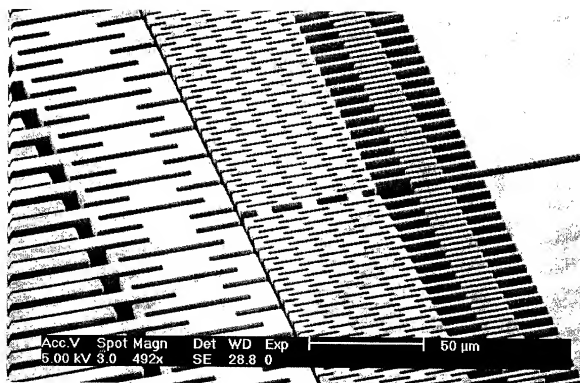


(c)



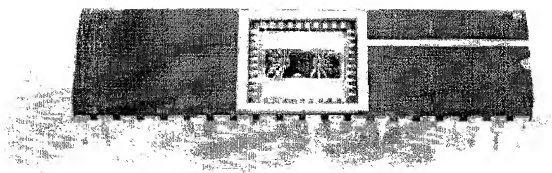
(d)

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(e)

FIG. 13



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FIG. 15

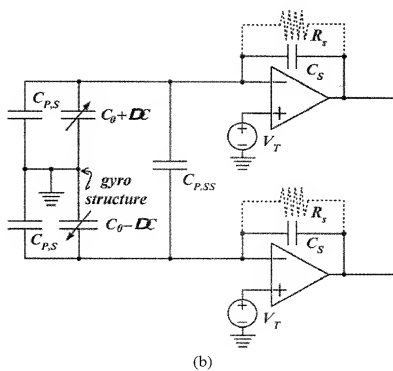
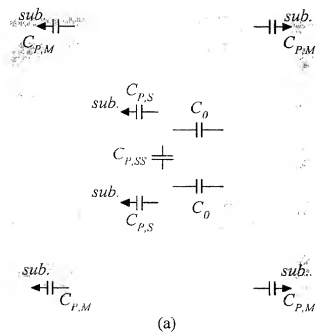
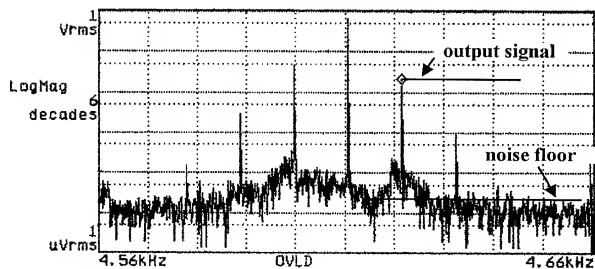


FIG. 16



(Y-axis corresponds to the root mean square voltage in Log-scale.)

FIG. 17

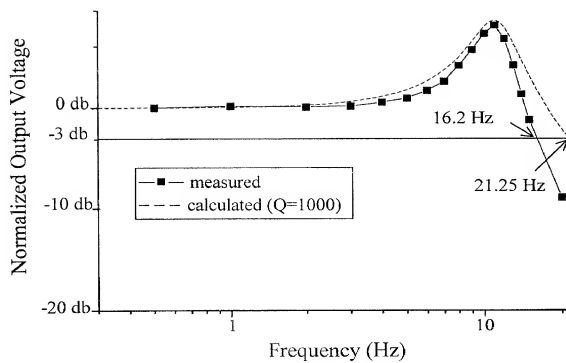


FIG. 18

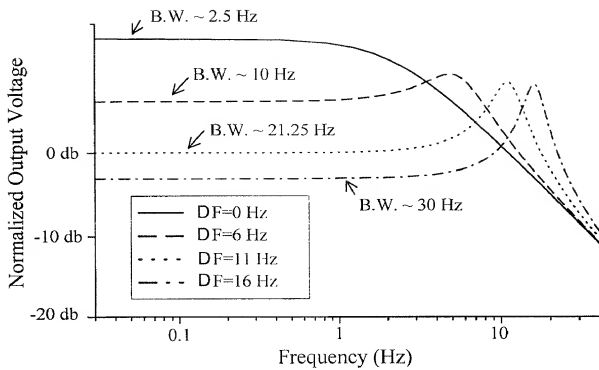


FIG. 19

